

Application Serial No. 10/785,259
Reply to Office Action of March 1, 2006

PATENT
Docket No. CU-3606

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Amendments To The Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1. (currently amended) A manufacturing method of a barrier-forming film comprising the steps of providing a vapor-deposited inorganic oxide film on a face of a substrate film, and applying an annealing treatment to the substrate film having said vapor-deposited inorganic oxide film,

wherein said substrate film comprises a resinous film which selected from a group consisting of polyesters, polyamides and polypropylenes; and

wherein said annealing treatment comprises a heating treatment carried out at a temperature within the range from 55 °C to 150 °C in order to cause thermal shrinkage of the substrate film and to increase density of the vapor-deposited inorganic oxide film.

2. (canceled)

3. (previously presented) A manufacturing method of a barrier-forming film according to claim 1, wherein said vapor-deposited inorganic oxide film comprises a vapor-deposited silicon oxide film or a vapor-deposited aluminum oxide film.

4-5. (canceled)

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6. (previously presented) A manufacturing method of a barrier-forming film according to claim 1, wherein said heating treatment is carried out for a heating treatment time within a range of from 30 minutes to five days.
7. (canceled)
8. (new) A manufacturing method of a barrier-forming film according to claim 1, wherein said substrate film to be treated has a residual stress of being in the range of from 0.1 to 1%, and wherein the thermal shrinkage of the substrate caused by the treatment is in the range of from -0.001 to -1.0% in at least any one of the flow direction and the width direction upon forming the film.
9. (new) A manufacturing method of a barrier-forming film according to claim 3, wherein said substrate film to be treated has a residual stress of being in the range of from 0.1 to 1%, and wherein the thermal shrinkage of the substrate caused by the treatment is in the range of from -0.001 to -1.0% in at least any one of the flow direction and the width direction upon forming the film.
10. (new) A manufacturing method of a barrier-forming film according to claim 6, wherein said substrate film to be treated has a residual stress of being in the range of from 0.1 to 1%, and wherein the thermal shrinkage of the substrate caused by the treatment is in the range of from -0.001 to -1.0% in at least any one of the flow direction and the width direction upon forming the film.